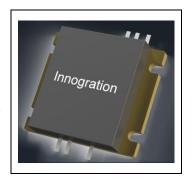
Innogration (Suzhou) Co., Ltd. Document Number: S2MAH0710-70H3P

0.7-1.0GHz, 70W, 2 stages GaN Fully matched PA

Description

The S2MAH0710-70H3P is a 70-watt Psat capable, 2 stage integrated IMFET, designed for broad band applications, with frequencies from 0.7 to 1.0GHz. The module is 50 Ω input/output matched and requires minimal external components, with DC block capacitor integrated inside When used at higher voltage like 32V, it can deliver up to 80W Psat across the full band The module implements multiple GaN active dice and its matching network within highly compact 30.8*27.4mm metal RF package with excellent capability for heat dissipation.



 $\mbox{V}_{\mbox{\footnotesize DS}}\mbox{= 28V, V}_{\mbox{\footnotesize gs1}}\mbox{= -3.2V, I}_{\mbox{\footnotesize dq1}}\mbox{= 200mA, V}_{\mbox{\footnotesize gs2}}\mbox{= -2.6V, I}_{\mbox{\footnotesize dq2}}\mbox{= 10mA ,Device screwed down}$

Freq (MHz)	P1(dBm)	P1 Gain (dB)	P3dB	P3dB	EFF (%)
			(dBm)	(W)	
700	46.86	30.5	48.77	75.4	55.2
750	46.58	30.9	48.29	67.5	52.2
800	46.36	31.3	48.07	64.1	50.6
850	46.84	32.1	48.15	65.4	53.3
900	47.59	32.0	48.38	68.9	57.3
950	47.84	31.8	48.55	71.6	56.3
1000	47.68	30.6	48.64	73.1	55.2

Applications

- P band power amplifier
- UHF power amplifier

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
DrainSource Voltage	$V_{\scriptscriptstyle DSS}$	150	Vdc
GateSource Voltage	$V_{\sf GS}$	-10 to +2	Vdc
Operating Voltage	V_{DD}	+36	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T _c	+150	°C
Operating Junction Temperature	Τ _J	+225	°C



TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (Pin=0dBm, Idq=200mA)

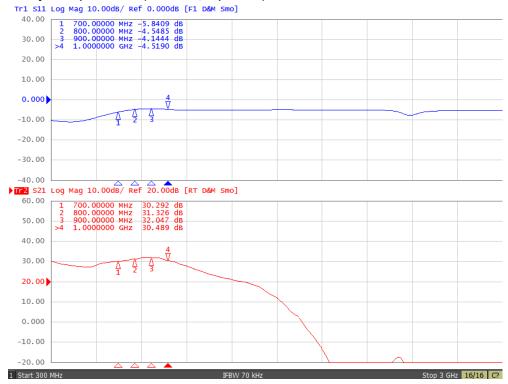
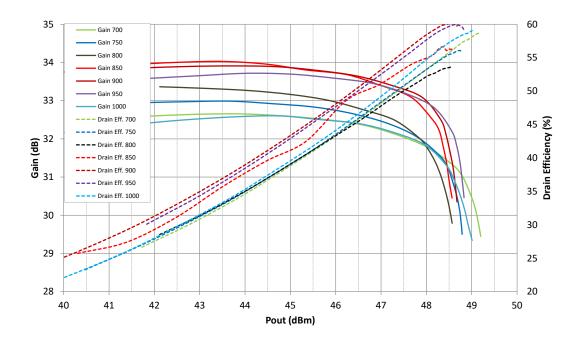
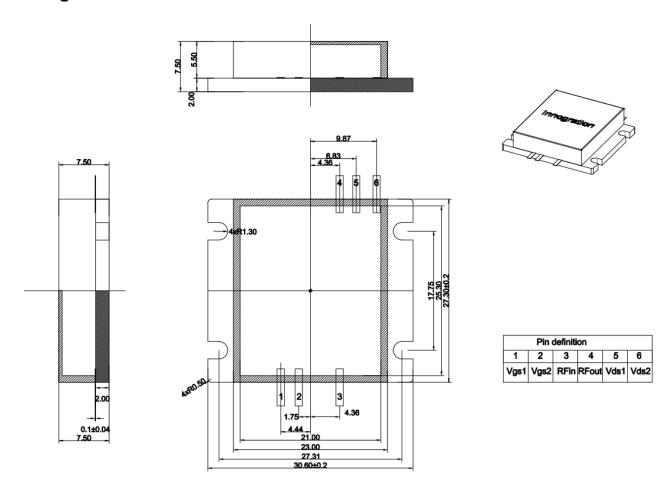


Figure 3. Pout, Eff, Gain, drain current Vs Frequency @28V



(Unit:mm) **Package Dimensions**



Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2025/6/12	Rev 1.0	Advanced Datasheet

Application data based on HJ-25-05

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